Docket No.: 51876P370

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

Young-Jin YOON

Application No.:

Filed:

For: SEMICONDUCTOR MEMORY DEVICE

HAVING ADVANCED PREFETCH BLOCK

Art Group:

Examiner:

#### INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Date: 7/1/03

Eric S. Hyman, Reg. No. 30,139

12400 Wilshire Blvd., 7th Floor Los Angeles, California 90025 (310) 207-3800 Substitute for form 1449A/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	1

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Complete if Known				
Application Number				
Filing Date				
First Named Inventor	Young-Jin YOON			
Art Unit				
Examiner Name				
Attorney Docket Number	51876P370			

	U.S. PATENT DOCUMENTS							
Examiner Cite		Document Number  Number - Kind Code <sup>2</sup> (if known)	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,		US-6,556,494 B2	04-29-2003	Morzano et al.				
		US-6,381,180 B1	04-30-2002	Merritt et al.				
		US-6,154,416	11-28-2000	Lee et al.				
,		US-6,085,300	07-04-2000	Sunaga et al.				
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	FOREIGN PATENT DOCUMENTS						
	Cite	Foreign Patent Document	1		Pages, Columns, Lines,		
	No.1	Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
1		10-040678	02-13-1998	Semiconductor Memory	Patent Abstract		
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Examiner Signature		Date Considere	ed	

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. <sup>6</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (05-03) as modified by Blakely, Solokoff, Taylor & Zafman (wir) 05/02/2003.

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<sup>/\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

## **Information Disclosure Statement**

## New U.S. Patent Application for SEMICONDUCTOR MEMORY DEVICE HAVING ADVANCED PREPATCH BLOCK Our Ref. No.: P03H1052/US/wy

## Reference No.:

- (1) US Patent No. 6,556,494
- (2) US Patent No. 6,381,180
- (3) US Patent No. 6,154,416
- (4) US Patent No. 6,085,300
- (5) US Patent No. 5,881,017
- (6) US Publication No. 2003/0021177 A1
- (7) US Publication No. 2002/0186608 A1
- (8) US Publication No. 2002/0131313 A1
- (9) JP Laid-Open No. 10-40678